

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1314	(gaas gallium adj arsenide) near2 substrate and (hemt hifet heterojunction adj (field fet))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/13 14:56
L3	571	L2 and ((aluminum and indium) or (ALGaAs or Gaalas) and (InGaAs or gainas))	US-PGPUB; USPAT	OR	OFF	2004/12/13 14:56
L4	1444	(257/192,194,195,280,284).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/13 14:56
L5	554	L4 and ((aluminum and indium) or (ALGaAs or Gaalas) and (InGaAs or gainas))	US-PGPUB; USPAT	OR	OFF	2004/12/13 14:56
L6	417	(L3 or L5) and ((carbon zinc) near2 (doped doping dope) or p-type)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/13 14:57
S1	1	("20040104404").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/13 11:36
S2	1314	(gaas gallium adj arsenide) near2 substrate and (hemt hifet heterojunction adj (field fet))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/13 12:19
S3	571	S2 and ((aluminum and indium) or (ALGaAs or Gaalas) and (InGaAs or gainas))	US-PGPUB; USPAT	OR	OFF	2004/12/13 12:07
S4	1444	(257/192,194,195,280,284).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/13 12:06
S5	554	S4 and ((aluminum and indium) or (ALGaAs or Gaalas) and (InGaAs or gainas))	US-PGPUB; USPAT	OR	OFF	2004/12/13 12:07
S6	343	S3 not S5	US-PGPUB; USPAT	OR	OFF	2004/12/13 12:07
S7	228	S3 and S5	US-PGPUB; USPAT	OR	OFF	2004/12/13 12:07

S8	10	nishi.in. and (hemt hfjet heterojunction adj (field fet))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/13 12:20
S9	53	(WADA bito nishi).in. and (hemt hfjet heterojunction adj (field fet))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/13 14:55